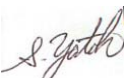

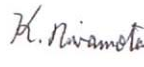


1. TYPE 2SCR523V1
2. STRUCTURE NPN SILICON EPITAXIAL PLANAR TRANSISTOR
3. APPLICATIONS GENERAL PURPOSE SMALL SIGNAL AMPLIFIER
4. ABSOLUTE MAXIMUM RATINGS [Ta=25°C]

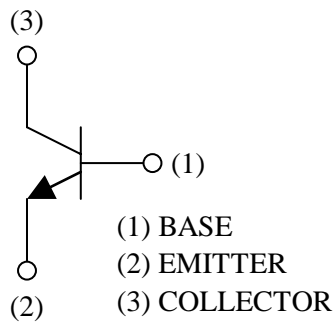
COLLECTOR-BASE VOLTAGE	$V_{CBO}$	...	50V
COLLECTOR-EMITTER VOLTAGE	$V_{CEO}$	...	50V
EMITTER-BASE VOLTAGE	$V_{EBO}$	...	5V
COLLECTOR CURRENT	$I_C$	...	100mA
	$I_{CP}$	...	200mA
			$P_W=10\text{ms}$ SINGLE PULSE
POWER DISSIPATION	$P_D$	...	100mW
			* EACH TERMINAL MOUNTED ON A REFERENCE LAND
JUNCTION TEMPERATURE	$T_j$	...	150°C
RANGE OF STORAGE TEMPERATURE	$T_{stg}$	...	-55~150°C

DESIGN	CHECK	APPROVAL	DATE : 23/ JUL / 2012	SPECIFICATION No. TSQ03131-2SCR523V1
			REV. : 0	<b>ROHM Co.,Ltd.</b>

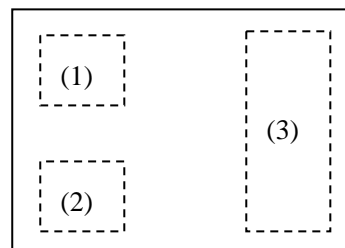
5. ELECTRICAL CHARACTERISTICS [Ta=25°C]

PARAMETER	SYMBOL	CONDITION	MIN.	TYP.	MAX.
COLLECTOR-EMITTER BREAKDOWN VOLTAGE	$BV_{CEO}$	$I_C=1mA$	50V	-	-
COLLECTOR-BASE BREAKDOWN VOLTAGE	$BV_{CBO}$	$I_C=50\mu A$	50V	-	-
EMITTER-BASE BREAKDOWN VOLTAGE	$BV_{EBO}$	$I_E=50\mu A$	5V	-	-
COLLECTOR CUT-OFF CURRENT	$I_{CBO}$	$V_{CB}=50V$	-	-	0.1 $\mu A$
EMITTER CUT-OFF CURRENT	$I_{EBO}$	$V_{EB}=5V$	-	-	0.1 $\mu A$
COLLECTOR-EMITTER SATURATION VOLTAGE	$V_{CE(sat)}$	$I_C=50mA / I_B=5mA$	-	0.10V	0.30V
DC CURRENT GAIN	$h_{FE}$	$V_{CE}=6V / I_C=1mA$	120	-	560
TRANSITION FREQUENCY	$f_T$	$V_{CE}=10V / I_E=-10mA$ $f=100MHz$	-	350MHz	-
OUTPUT CAPACITANCE	$C_{ob}$	$V_{CB}=10V / I_E=0A$ $f=1MHz$	-	1.6pF	-

6. INTERNAL CIRCUIT



TOP VIEW



7. MARKING



“ NB “ MEANS 2SCR523V1

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